

determining the voltage level of the programming pulse used to program a fast bit of said memory array having a relatively faster programming characteristic than other bits in said array; and

setting an initial programming pulse voltage level to a level near said programming pulse voltage level of said fast bit.

3. A method according to claim 2 and wherein said step of determining includes:

programming a small set of bits of said memory array;

setting a starting programming pulse voltage level to a programming pulse voltage level not higher than a programming pulse voltage level used to program a fast bit of said small set having a relatively faster programming characteristic than other bits in said small set;

programming generally all of the bits of said memory array using pulses having voltage levels beginning at said starting programming pulse voltage level; and

setting said initial programming pulse voltage level to a programming pulse level near a programming pulse voltage level used to program a bit having a relatively faster programming characteristic than generally all other bits of said array.

4. A method according to claim 2 wherein said initial programming pulse voltage level is not higher than said programming pulse level of said fast bit.

5. A method according to claim 3 wherein said generally all of bits of said array does not include bits of said small set.

6. A method according to claim 3 wherein said generally all of bits of said array does include bits of said small array.

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